

Ultraprecision CD Metrology for Sub-100 nm Patterns by AFM

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Outline

- 1. Introduction
- 2. Metrological AFM design Novel 3D scanner, compact laser interferometers
- 3. Interferometer performance Resolution / linearity
- 4. Apparent linewidth repeatability Optimization / preliminary demonstration
- 5. Stage positioning Optimization / minimization of drift
- 6. Summary and future work

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Lithography requirements





Metrological improvement in AFM

Category	Items to be solved
AFM tip	Radius of curvature, Tip artifact, Tip wear / broken
Scanning technology	Straightness, Orthogonality, Mechanical vibration, Scheme of servo control
Linearity	Resolution / precision of displacement sensor
Profile analysis	Deconvolution of profile data, Definition of CD
Environment control	Floor vibration, Acoustic noise, Temperature fluctuation





MIRAI AFM Set up



Goal:

Development of precision AFM for nanometerscale dimensional measurement :

Tool precision: 0.3 nm in 2007

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Configuration of AFM unit





IRAI

MIRAL Uncertainty consideration in angular motion





AIRAI Optical design of interferometer

- differential scheme
- double pass
- Michelson type
- homodyne
- wavelength is calibrated ($\Delta \sim 10^{-9}$)





Signal processing diagram







Result of correction





Reduction of mechanical vibration







Resolution





Measurement of apparent linewidth

- Scanning is servo-controlled
- Three-dimensional coordinates







Cross-sectional profiles



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AIRAI Repeatability of apparent linewidth









Backlash and drift at a stop



Optimum condition : backlash / drift





- High-resolution interferometer system was constructed and installed in a metrological AFM.
- Linearity has been improved better than 0.15 nm(p-p) by DSP based, cyclic error correction system.
- Resolution better than 0.05 nm for the system of the laser interferometer and 3D fine-motion scanner was demonstrated.
- Repeatability of apparent linewidth reached 0.5-1.0 nm(3σ).

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Achieving of the measurement accuracy of 0.3-0.5 nm(3σ) for dynamic repeatability.

Investigating the influence of probe deformation on the measurement uncertainty.

